



瑞而美 work steadily

蘇州瑞而美光電科技有限公司

Suzhou Realmay Lightings Tech Co., Ltd

Specification of 2 inch GaN Substrate

Description	Specification
Material	2 inch GaN Substrate (Semi-Insulating)
Substrate Orientation	C-Plane (0001) off Angle $0.35^{\circ} \pm 0.15^{\circ}$ to M axis
Primary Flat Orientation & Length	(1-100) $\pm 0.5^{\circ}$, 16 ± 1.0 mm
Secondary Flat Orientation & Length	(11-20) $\pm 3.0^{\circ}$, 8 ± 1.0 mm
Diameter	50.0 ± 0.5 mm
Sapphire Substrate Thickness	350 ± 25 um
Useable Surface Area	> 90%
TTV	≤ 15 um
BOW	≤ 20 um
Front Surface Roughness	$Ra \leq 0.2$ nm
Back Surface Roughness	$Ra \leq 0.2$ nm
Resistivity (300K)	$> 10^6$ ohm.cm
Dislocation density	$< 1 \sim 9 \times 10^5 / \text{cm}^{-2}$
Laser Marking	As Substrate Laser Marking
Packaging	Clean room, vacuum packing

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